

Depletion-Mode Power MOSFET

General Features

- Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- ESD Improved Capability
- Fast Switching Speed
- RoHS Compliant
- Halogen-free Available

BV_{DSX}	R_{DS(ON)} (Max.)	I_D
100V	3.0Ω	0.3A

Applications

- Suppressing Surge Current
- Normally-on Switches
- Constant Current Source
- Protection Circuits



Ordering Information

Part Number	Package	Marking	Remark
DMX1072	SOT-89	1072	Halogen Free
DMS1072	SOT-223	1072	Halogen Free

Absolute Maximum Ratings

T_A=25°C unless otherwise specified

Symbol	Parameter	DMX1072	DMS1072	Unit
V _{DSX}	Drain-to-Source Voltage ^[1]	100		V
V _{DGX}	Drain-to-Gate Voltage ^[1]	100		V
I _D	Continuous Drain Current	0.3		A
I _{DM}	Pulsed Drain Current ^[2]	1.2		
P _D	Power Dissipation	1.0	1.5	W
	Derating Factor above 25°C	0.008	0.012	W/°C
V _{GS}	Gate-to-Source Voltage	±20		V
V _{ESD(G-S)}	Gate Source ESD IEC, C=150pF, R=330Ω	1500		V
T _L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300		°C
T _J and T _{STG}	Operating and Storage Temperature Range	-55 to 150		

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	DMX1072	DMS1072	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	125	83	K/W

Electrical Characteristics

OFF Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	100	--	--	V	$V_{GS} = -5\text{V}, I_D = 250\mu\text{A}$
$I_{D(OFF)}$	Drain-to-Source Leakage Current	--	--	1	μA	$V_{DS} = 100\text{V}, V_{GS} = -5\text{V}$
		--	--	1	mA	$V_{DS} = 100\text{V}, V_{GS} = -5\text{V}$ $T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	20	μA	$V_{GS} = +20\text{V}, V_{DS} = 0\text{V}$
		--	--	-20		$V_{GS} = -20\text{V}, V_{DS} = 0\text{V}$

ON Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_{DSS}	Saturated Drain-to-Source Current	0.3	--	--	A	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	--	3.0	Ω	$V_{GS} = 0\text{V}, I_D = 0.15\text{A}$ ^[3]
		--	--	2.8	Ω	$V_{GS} = 5\text{V}, I_D = 0.15\text{A}$ ^[3]
$V_{GS(OFF)}$	Gate-to-Source Cut-off Voltage	-3.3	--	-1.5	V	$V_{DS} = 3\text{V}, I_D = 8\mu\text{A}$
gfs	Forward Transconductance	--	0.46	--	S	$V_{DS} = 20\text{V}, I_D = 0.15\text{A}$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{ISS}	Input Capacitance	--	81.3	--	pF	$V_{GS} = -5\text{V}$ $V_{DS} = 25\text{V}$ $f = 1.0\text{MHz}$
C_{OSS}	Output Capacitance	--	32.7	--		
C_{RSS}	Reverse Transfer Capacitance	--	6.6	--		
Q_G	Total Gate Charge	--	2.52	--	nC	$V_{GS} = -5\text{V} \sim 5\text{V}$ $V_{DS} = 50\text{V}, I_D = 0.15\text{A}$
Q_{GS}	Gate-to-Source Charge	--	0.69	--		
Q_{GD}	Gate-to-Drain (Miller) Charge	--	0.7	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	6.2	--	ns	$V_{GS} = -5\text{V} \sim 5\text{V}$ $V_{DD} = 50\text{V}, I_D = 0.15\text{A}$ $R_G = 10\Omega$
t_{rise}	Rise Time	--	4.8	--		
$t_{d(OFF)}$	Turn-off Delay Time	--	11.6	--		
t_{fall}	Fall Time	--	17	--		

Source-Drain Diode Characteristics $T_A=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Units	Test Conditions
V_{SD}	Diode Forward Voltage	--	--	1.5	V	$I_{SD}=0.15\text{A}$, $V_{GS}=-10\text{V}$

NOTE:

[1] $T_J=+25^{\circ}\text{C}$ to $+150^{\circ}\text{C}$

[2] Repetitive rating, pulse width limited by maximum junction temperature.

[3] Pulse width $\leq 380\mu\text{s}$; duty cycle $\leq 2\%$.

Typical Characteristics

Figure 1. Maximum Power Dissipation vs. Case Temperature

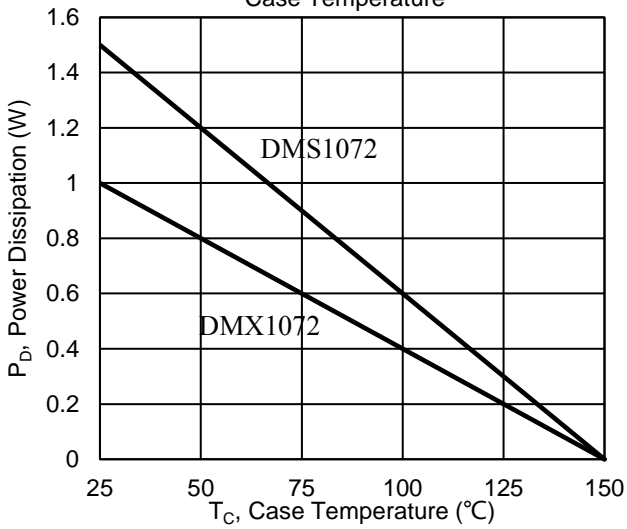


Figure 2. Maximum Continuous Drain Current vs Case Temperature

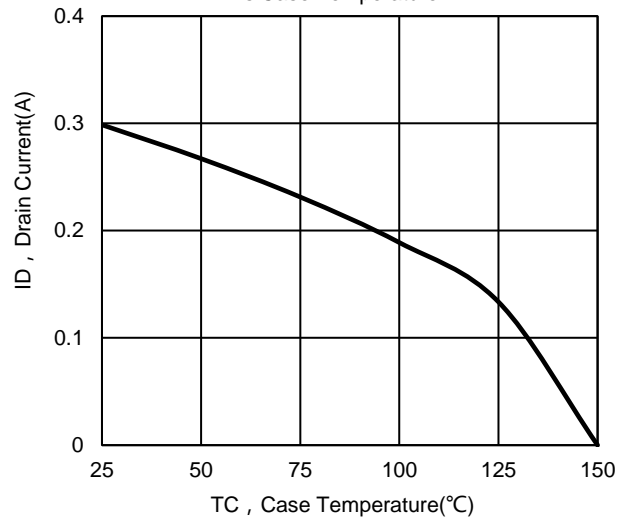


Figure 3. Typical Output Characteristics

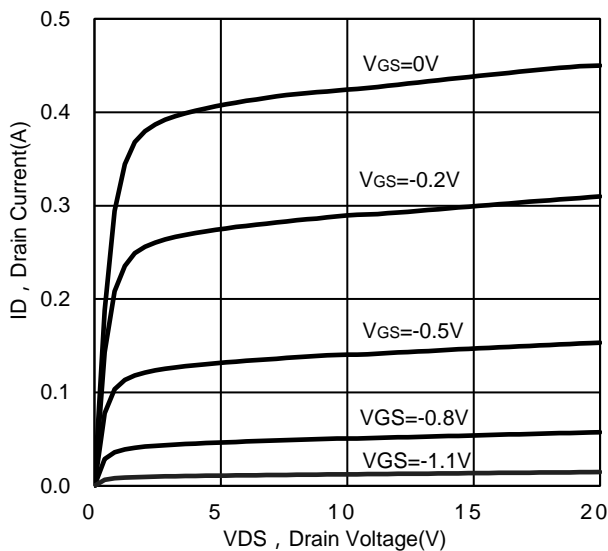


Figure 4. Typical Transfer Characteristics

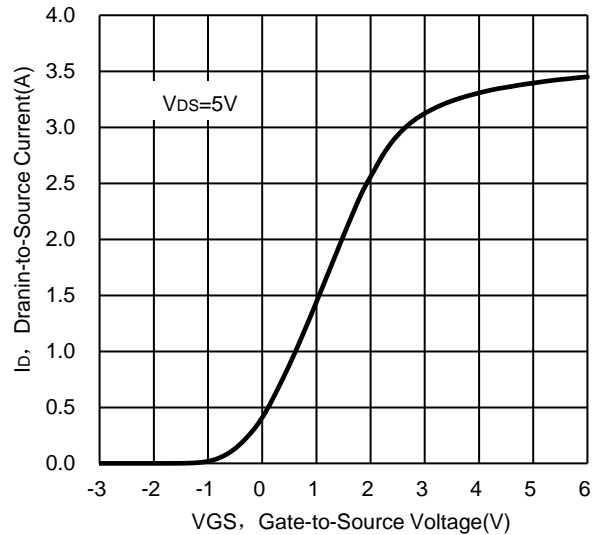
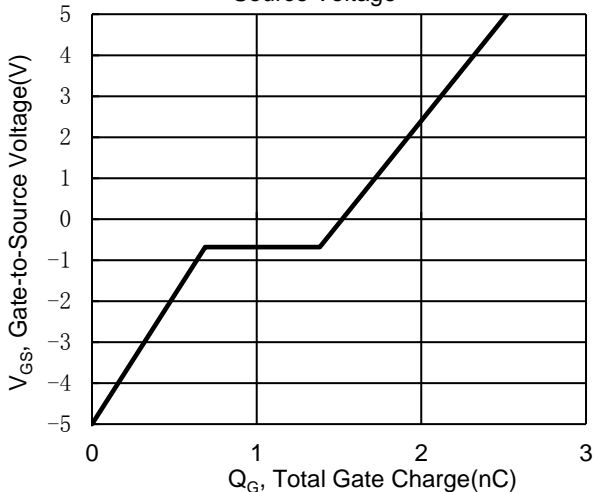
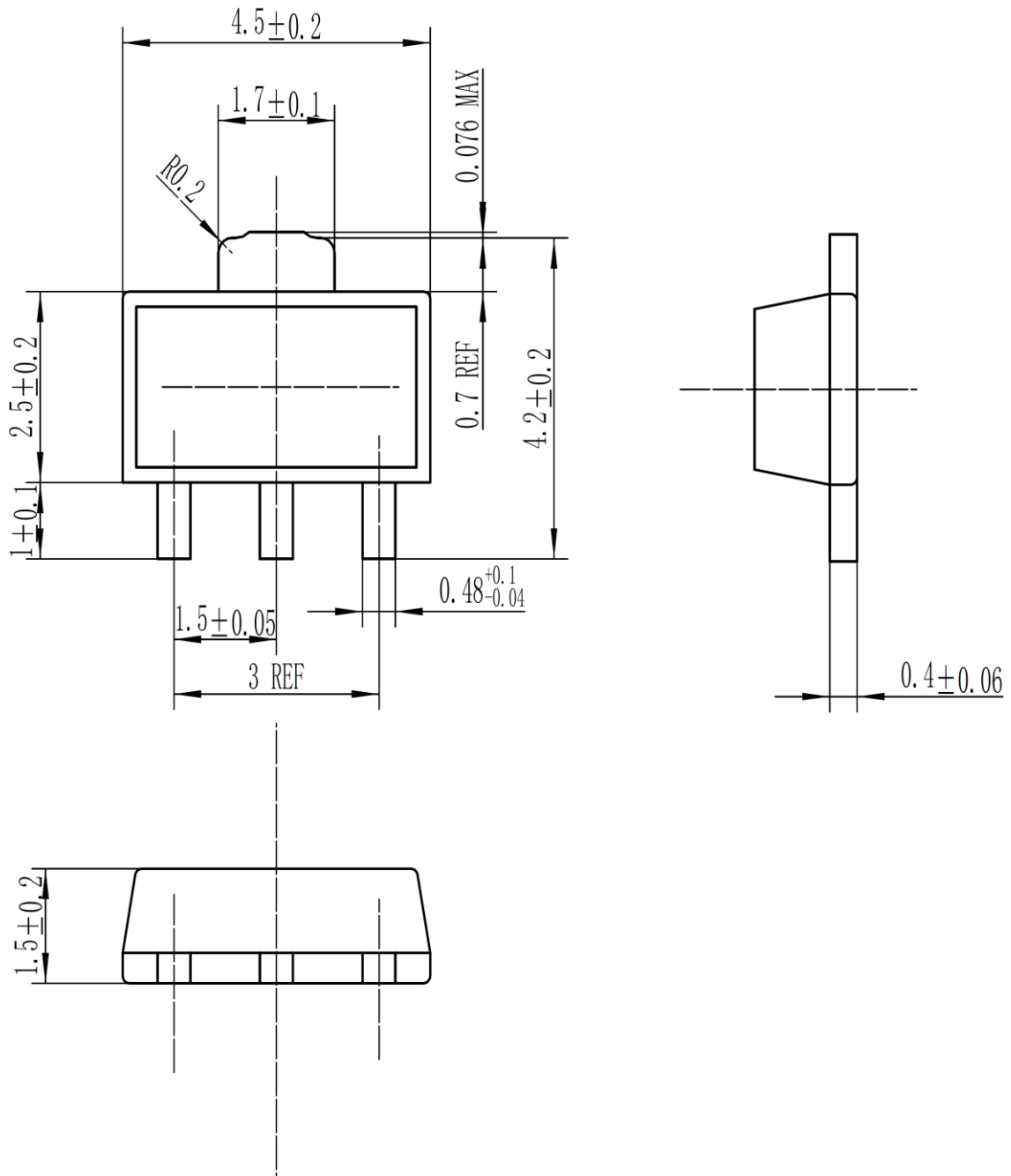


Figure 5. Typical Gate Charge vs. Gate-to-Source Voltage

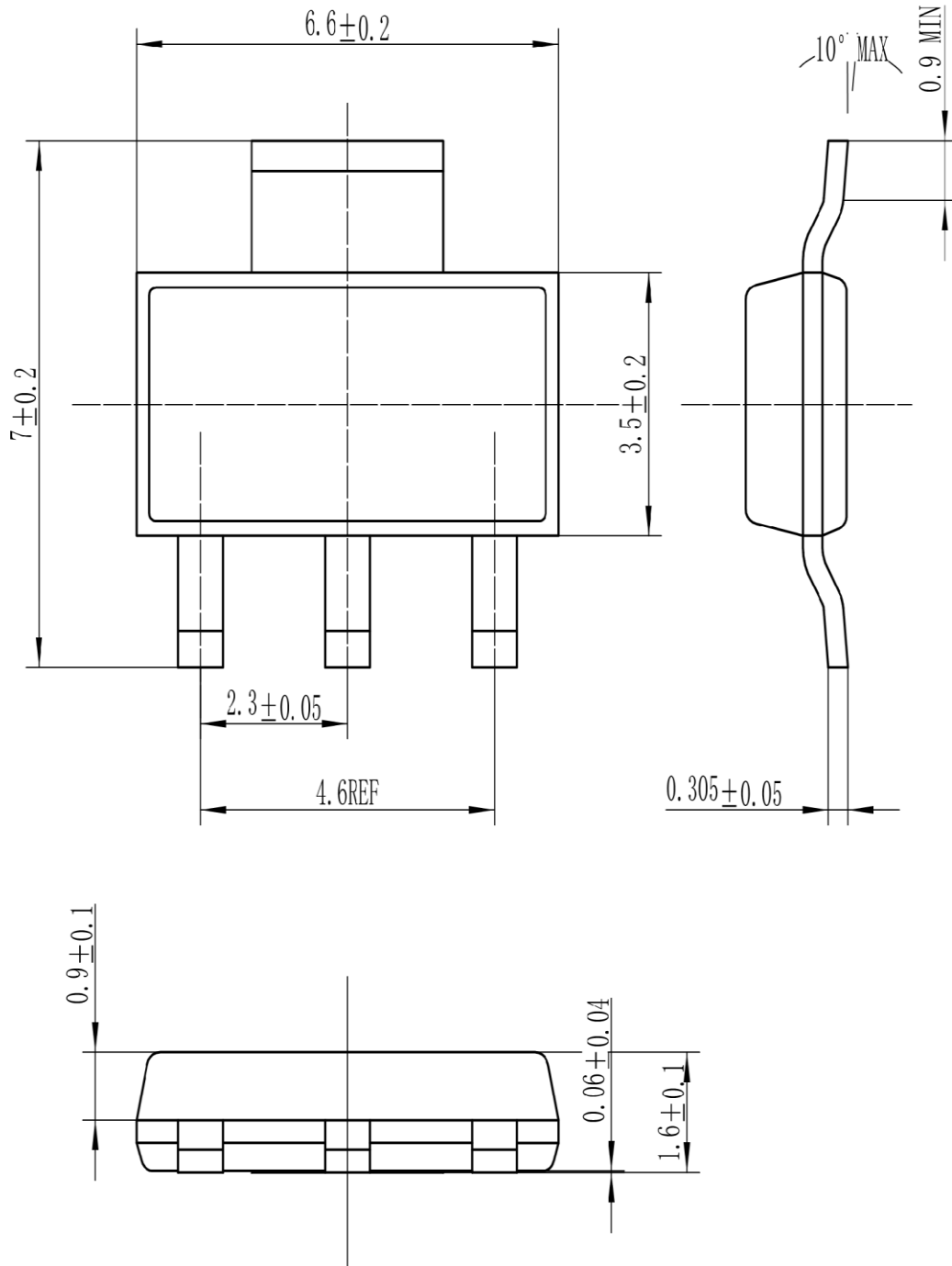


Package Dimensions

SOT-89



SOT-223





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